

Maximum Ratings at Tj = 25 °C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	60	V
Drain source voltage for short circuit protection	V _{DS(SC)}	32	
Continuous input current 1) I _{IN}			mA
$-0.2V \le V_{1N} \le 10V$		no limit	
V_{1N} < -0.2V or V_{1N} > 10V		<i>I</i> _{IN} ≤ 2	
Operating temperature	T_{j}	- 40 +150	°C
Storage temperature	$T_{\rm stg}$	- 55 + 150	
Power dissipation	P_{tot}	50	W
T _C = 25 °C			
Unclamped single pulse inductive energy	E _{AS}	1000	mJ
$I_{D(ISO)} = 3.5 A$			
Electrostatic discharge voltage (Human Body Model)	V _{ESD}	3000	V
according to MIL STD 883D, method 3015.7 and			
EOS/ESD assn. standard S5.1 - 1993			
Load dump protection $V_{\text{LoadDump}}^{(2)} = V_{\text{A}} + V_{\text{S}}$	V_{LD}		
$V_{\rm IN}$ =low or high; $V_{\rm A}$ =13.5 V			
$t_d = 400 \text{ ms}, R_I = 2 \Omega, I_D = 0.5*3.5A$		75	
$t_d = 400 \text{ ms}, R_l = 2 \Omega, I_D = 3.5 \text{A}$		70	

Thermal resistance

junction - case:	R _{thJC}	2.5	K/W
junction - ambient:	R_{thJA}	75	
SMD version, device on PCB: 3)	R_{thJA}	45	

¹In case of thermal shutdown a minimum sensor holding current of 500 µA has to be guaranteed (see also page 3).

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 $^{^{2}\}textit{V}_{\text{Loaddump}}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

 $^{^3}$ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm 2 (one layer, 70 μ m thick) copper area for Drain connection. PCB mounted vertical without blown air.



Electrical Characteristics

Parameter	Symbol		Values		Unit	
at T _j =25°C, unless otherwise specified	=25°C, unless otherwise specified		typ.	max.	<u> </u>	
Characteristics	•	•	•	•	•	
Drain source clamp voltage	V _{DS(AZ)}	60	-	73	V	
$T_{\rm j}$ = - 40+ 150°C, $I_{\rm D}$ = 10 mA						
Off state drain current	I _{DSS}	5 μ.		μA		
$V_{DS} = 32 \text{ V}, T_j = -40+150 °C, V_{IN} = 0 \text{ V}$						
Input threshold voltage $V_{\text{IN(th)}}$		1.3	1.7	2.2	V	
$I_{\rm D} = 0.7 {\rm mA}$						
Input current - normal operation, $I_D < I_{D(lim)}$:	/IN(1)	-	30	60	μΑ	
V _{IN} = 10 V						
Input current - current limitation mode, $I_D = I_{D(lim)}$:	I _{IN(2)}	-	120	300		
V _{IN} = 10 V						
Input current - after thermal shutdown, $I_D=0$ A:	I _{IN(3)} 800 2200 4000					
_V _{IN} = 10 V						
Input holding current after thermal shutdown 1)	I _{IN(H)}					
$T_{\rm j}$ = 25 °C		500	_	-		
_T _j = 150 °C		300	-	-		
On-state resistance	R _{DS(on)}				mΩ	
V_{IN} = 5 V, I_{D} = 3.5 A, T_{j} = 25 °C		-	90	120		
$V_{\rm IN}$ = 5 V, $I_{\rm D}$ = 3.5 A, $T_{\rm j}$ = 150 °C		-	180	240		
On-state resistance	R _{DS(on)}					
V_{IN} = 10 V, I_{D} = 3.5 A, T_{j} = 25 °C		-	80	100		
$V_{\rm IN}$ = 10 V, $I_{\rm D}$ = 3.5 A, $T_{\rm j}$ = 150 °C			160	200		
Nominal load current (ISO 10483)	I _{D(ISO)}	3.5	-	-	Α	
V_{IN} = 10 V, V_{DS} = 0.5 V, T_{C} = 85 °C						

¹lf the input current is limited by external components, low drain currents can flow and heat the device. Auto restart behaviour can occur.

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Electrical Characteristics

Parameter	Symbol	Values			Unit	
T _j =25°C, unless otherwise specified		min.	typ.	max.		
Characteristics	,			•		
Initial peak short circuit current limit	I _{D(SCp)}	-	25	-	Α	
V_{IN} = 10 V, V_{DS} = 12 V						
Current limit 1)	/ _{D(lim)} 7 10			15		
$V_{\rm IN}$ = 10 V, $V_{\rm DS}$ = 12 V, $t_{\rm m}$ = 350 μ s,						
$T_{\rm j}$ = -40+150 °C						
Dynamic Characteristics	·		•		•	
Turn-on time V_{IN} to 90% I_{D} :	t _{on}	-	40	70	μs	
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V						
Turn-off time V_{IN} to 10% I_D :	$t_{\rm off}$	-	70	150		
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V						
Slew rate on 70 to 50% $V_{\rm bb}$:	-dV _{DS} /dt _{on}	-	1	3	V/µs	
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V						
Slew rate off 50 to 70% V_{bb} :	dV _{DS} /dt _{off}	-	1	3		
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V						
Protection Functions ²⁾						
Thermal overload trip temperature	T _{it}	150	165	-	°C	
Unclamped single pulse inductive energy	E _{AS}				mJ	
$I_{\rm D}$ = 3.5 A, $T_{\rm j}$ = 25 °C, $V_{\rm bb}$ = 32 V		1000				
$I_{\rm D}$ = 3.5 A, $T_{\rm j}$ = 150 °C, $V_{\rm bb}$ = 32 V		225				
Inverse Diode						
Inverse diode forward voltage	V _{SD}	-	1	-	V	
$I_{F} = 5*3.5A$, $t_{m} = 300 \ \mu S$, $V_{IN} = 0 \ V$						

¹Device switched on into existing short circuit (see diagram Determination of I $_{D(lim)}$). If the device is in on condition and a short circuit occurs, these values might be exceeded for max. 50 μ s.

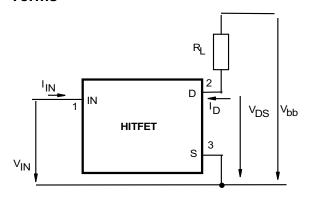
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²Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation

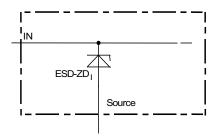


Block Diagramm

Terms

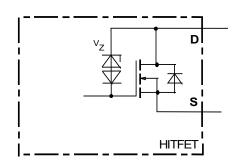


Input circuit (ESD protection)

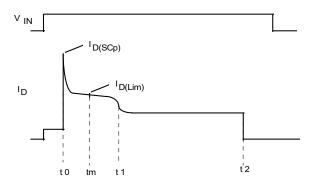


ESD zener diodes are not designed for DC current > 2 mA @ V_{IN} >10V.

Inductive and overvoltage output clamp



Short circuit behaviour



t₀: Turn on into a short circuit

t_m: Measurementpoint for I_{D(lim)}

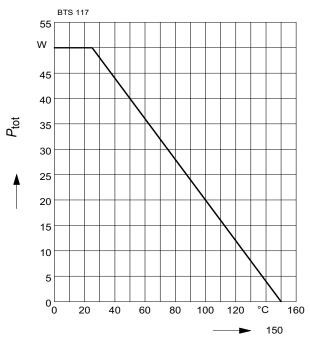
t₁: Activation of the fast temperature sensor and regulation of the drain current to a level where the junction temperature remains constant.

t2: Thermal shutdown caused by the second temperature sensor, achieved by an integrating measurement.

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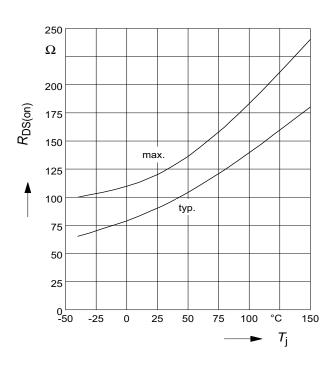


Maximum allowable power dissipation $P_{tot} = f(T_c)$



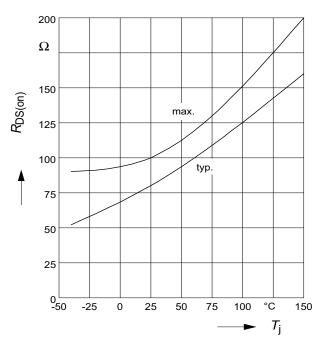
On-state resistance

$$R_{ON} = f(T_i); I_D = 3.5A; V_{IN} = 5V$$



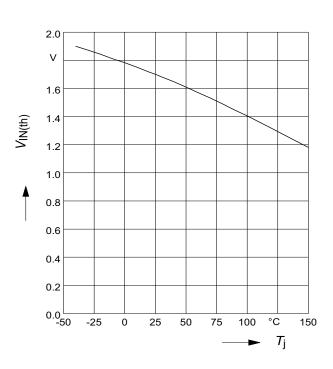
On-state resistance

$$R_{ON} = f(T_i); I_D = 3.5A; V_{IN} = 10V$$



Typ. input threshold voltage

$$V_{IN(th)} = f(T_i); I_D=0.7mA; V_{DS}=12V$$

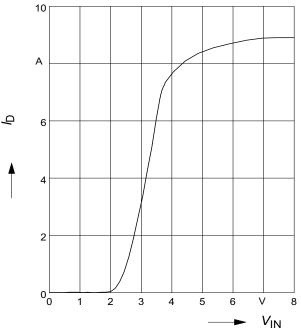


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Typ. transfer characteristics

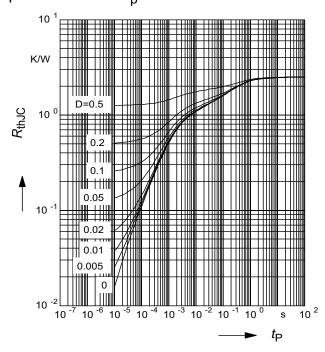
$$I_D = f(V_{IN}); V_{DS}=12V; T_j=25$$
°C



Transient thermal impedance

$$Z_{\mathsf{thJC}} = f\left(t_{\mathsf{p}}\right)$$

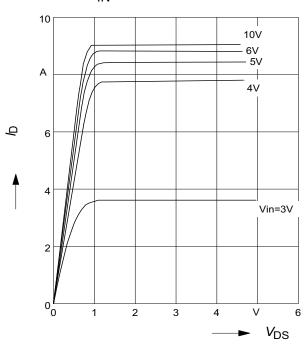
parameter : $D = t_p/T$



Typ. output characteristic

 $I_D = f(V_{DS}); T_j = 25$ °C

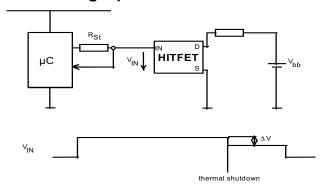
Parameter: V_{IN}





Application examples:

Status signal of thermal shutdown by monitoring input current



$$\Delta V = R_{ST} * I_{IN(3)}$$



Package Outlines

1 Package Outlines

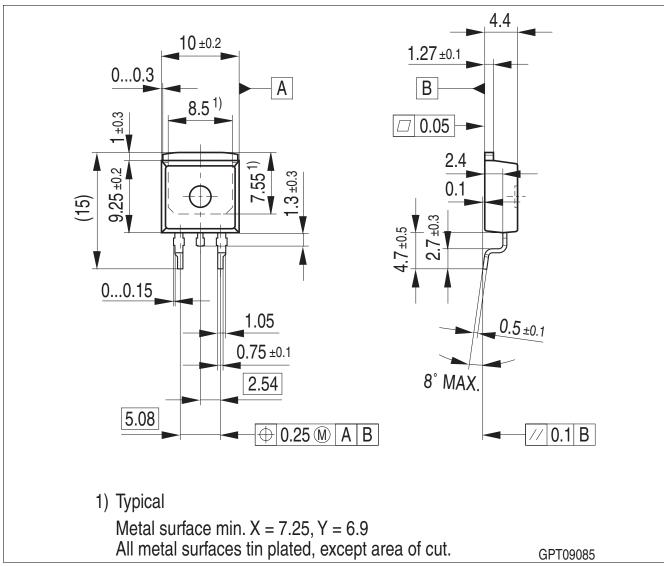


Figure 1 PG-TO263-3-2 (Plastic Dual Small Outline Package) (RoHS-Compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Please specify the package needed (e.g. green package) when placing an order

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.

Dimensions in mm



Revision History

2 Revision History

Version	Date	Changes
Rev. 1.0	2009-07-20	intial released Datasheet

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